EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	668	dummy adj capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L2	217	L1 and dram	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L3	277	sram and ferroelectric and @ad<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L4	232	(ferroelectric or high-k sbt pzt) near gate adj (insulator insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L5	2379	gate adj dielectric with high-k	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L6	175	dummy adj gate with (periphery peripheral surround surrounding). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L7	57	"4873664" and (dummy inoperable) with (electrode capacitor transistor) and (ferroelectric or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52

L8	9420	(MATSUDA-A$ or NAGANO-Y$ OR UEMOTO-Y$ OR FUJII-E$).IN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L9	3	L8 and (dummy inoperable) with transistor not (ferroelectric or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L10	9	feram and dram and ferroelectric.detx. and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L11	8	("5281555" | "5300814" | "5300816" | "5689126" | "5777358" | "5895963" | "5913150" | "5943591").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/02 10:52
L12	1	(US-5361234-$).did.	USPAT	OR	OFF	2008/05/02 10:52
L13	4	L8 and (dummy inoperable) with transistor and (ferroelectric or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L14	7	L13 or L9	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L15	7	("4902646" | "5225704" | "5278105" | "5281555" | "5410161" | "5441915" | "5441916").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/02 10:52
L16	296	dummy adj gate with (periphery peripheral surround surrounding)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L17	1	L12 and boundary adj area with dummy.detx.	USPAT	OR	OFF	2008/05/02 10:52
L18	7165	(257/295,213,296, E21.664,E27.104).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/02 10:52

L19	442	L18 and dummy	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L20	82	L19 and @ad<"19971224"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L21	33	L20 not dummy adj (cell word adj line)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L22	4	L15 and dummy with gate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L23	731	gate adj (insulator insulating) near3 (ferroelectric or high-k sbt pzt)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L24	10	("5959878" "5281555" "5430671") and dummy and array	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L25	2	("5361224" | "5426315"). PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/02 10:52
L26	7	sram and gate adj (oxide dielectric insulator insulating) near3 ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L27	64	L18 and dummy adj gate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L28	6	sram and gate adj (oxide dielectric insulator insulating) near3 ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52

L29	6	"6320214"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L30	5189	feram dram and ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L31	180	(feram or dram and ferroelectric).detx. and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L32	43	L8 and (dummy inoperable)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L33	4	JP-09321248-$ or JP-11251554-$	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L34	15	(US-6320214-$ or US-5946563-$ or US-5689456-$ or US-5913150-$ or US-6150689-$ or US-5694353-$ or US-5959878-$ or US-5396100-$ or US-6018215-$ or US-5689126-$ or US-6091097-$ or US-5430671-$ or US-5281555-$ or US-5361224-$).did. or (JP-57180182-$).did.	USPAT; JPO	OR	OFF	2008/05/02 10:52
L35	5	(dish dishing) with dummy with capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52

L36	76	L31 and (pzt bto sbt strontium near barium near3 (taltalate titanate)). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L37	32	("5959878" "5281555" "5430671") and dummy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L38	5	L11 and gate.detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L39	5	L6 and @ad<"19971211" and dummy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L40	141	L31 and (capacitor pzt bto sbt strontium near barium near3 (taltalate titanate)). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L41	28	("5959878" "5281555" "5430671") and dummy. detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L42	105	dummy with capacitor with layers and (dummy dummies capacitors cell cells wordline wordlines). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L43	2	(("5,396,100") or ("5,913,150")).PN.	US-PGPUB; USPAT	OR	OFF	2008/05/02 10:52
L44	11	feram and dram and ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52

L45	76	L31 and capacitor.detx. and (pzt bto sbt strontium near barium near3 (taltalate titanate)).detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L46	138	gate adj (insulator insulating oxide dielectric) with ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 10:52
L47	139	L1 and (ferroelectric perovskite)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52
L48	65	L47 and (dram 1T near3 1C)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 10:52

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